



# N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)						
12	0.0198 at V <sub>GS</sub> = 4.5 V	4.5							
	0.0222 at V <sub>GS</sub> = 2.5 V	4.5	13.7 nC						
	0.0264 at V <sub>GS</sub> = 1.8 V	4.5							

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 % R<sub>q</sub> Tested

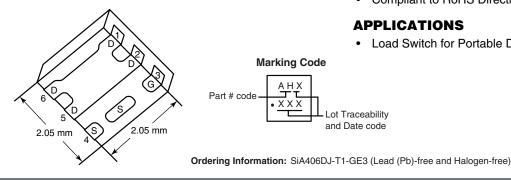
**APPLICATIONS** 

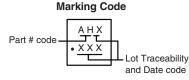
Compliant to RoHS Directive 2002/95/EC



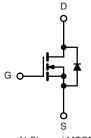
HALOGEN **FREE** 

#### PowerPAK SC-70-6L-Single





· Load Switch for Portable Devices



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T <sub>A</sub> = 25 °C, unle:	ss otherwise n	oted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	12	V	
Gate-Source Voltage		$V_{GS}$	± 8		
	T <sub>C</sub> = 25 °C		4.5 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 70 °C	I <sub>D</sub>	4.5 <sup>a</sup>		
Continuous Diain Current (1) = 150 °C)	T <sub>A</sub> = 25 °C		4.5 <sup>a, b, c</sup>		
	T <sub>A</sub> = 70 °C		4.5 <sup>a, b, c</sup>	Α	
Pulsed Drain Current		I <sub>DM</sub>	20		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	4.5 <sup>a</sup>		
Continuous Cource-Drain Diode Current	T <sub>A</sub> = 25 °C	'S	2.9 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		19		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	$P_{D}$	12	w	
Maximum rower Dissipation	T <sub>A</sub> = 25 °C	י ט	3.5 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Ra	inge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	7 0/**				

#### Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

# SiA406DJ

# Vishay Siliconix



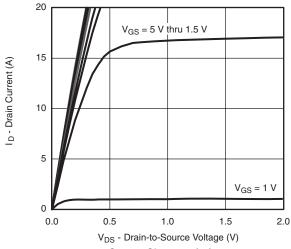
<b>SPECIFICATIONS</b> $T_J = 25  ^{\circ}\text{C}$			Min	T	Mess	11 14
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static  Drain Course Breakdown Voltage	T v/ T	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	10	<u> </u>	1	V
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	12	44		V mV/°C
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		11		
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	V V 1 252 A		- 2.9		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4		1.0	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
	500	$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$		20		Α
		$V_{GS} = 4.5 \text{ V}, I_D = 10.8 \text{ A}$		0.0165	0.0198	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 10.2 \text{ A}$		0.0185	0.0222	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 3 A		0.0220	0.0264	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 6 V, I <sub>D</sub> = 10.8 A		38		S
Dynamic <sup>b</sup>	<u>'</u>	,		•		
Input Capacitance	C <sub>iss</sub>			1380		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 0 V, f = 1 MHz		345		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	20 00		155		
		V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 10.8 A		15.2	23	nC
Total Gate Charge	$Q_g$	D3 - 7 d3 - 7 D		13.7	21	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10.8 A		2.6		
Gate-Drain Charge	Q <sub>gd</sub>	103 0 1, 103 110 1, 10 101011		1.1		
Gate Resistance	R <sub>q</sub>	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	1 - 1 1011 12	0.0	10	20	
Rise Time	t <sub>r</sub>	$V_{DD} = 6 \text{ V}, R_1 = 0.7 \Omega$		9	18	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 8.6 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		40	60	
Fall Time	t <sub>f</sub>	.b = 0.0 1 % 1 GEN		14	21	
Turn-On Delay Time				6		ns
	t <sub>d(on)</sub>	V 0VD 070			12	
Rise Time	t <sub>r</sub>	$V_{DD} = 6 \text{ V}, R_L = 0.7 \Omega$		11	17	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 8.6 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$		27	41	
Fall Time	t <sub>f</sub>			9	18	
Drain-Source Body Diode Characterist	1 1	T 05.00				
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			4.5 <sup>c</sup>	Α
ulse Diode Forward Current I <sub>SM</sub>					20	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 8.6 A, V <sub>GS</sub> = 0 V		8.0	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			22	33	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 8.6 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		7	14	nC
Reverse Recovery Fall Time	t <sub>a</sub>	3.3 π, απαι – 100 π/μο, 1 <sub>J</sub> – 20 0		8		ns
Reverse Recovery Rise Time	t <sub>b</sub>			14		

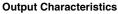
- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Package limited

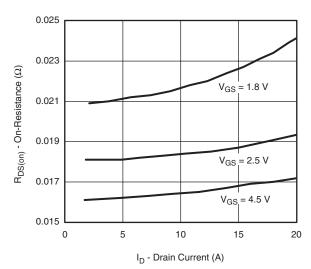
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



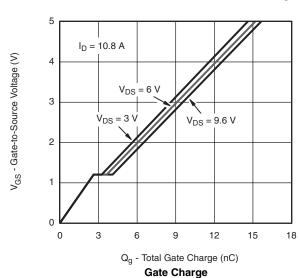
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

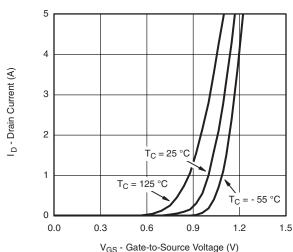




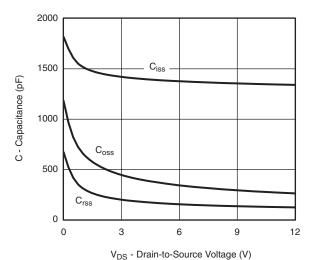


#### On-Resistance vs. Drain Current and Gate Voltage

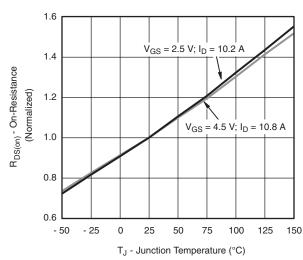




Transfer Characteristics



Capacitance

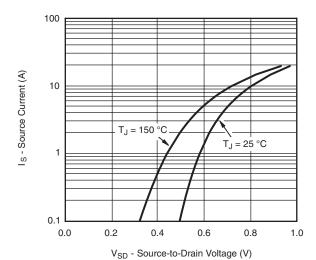


On-Resistance vs. Junction Temperature

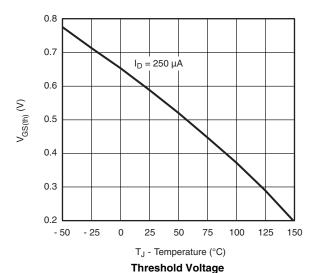
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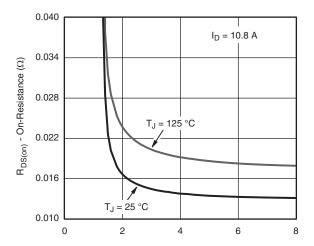
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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

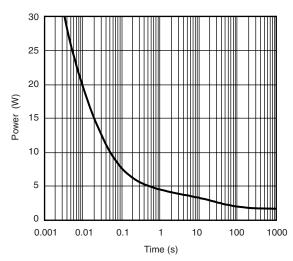


Soure-Drain Diode Forward Voltage

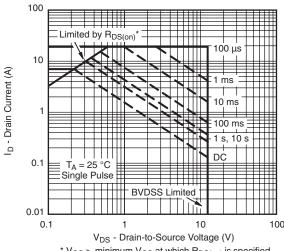




V<sub>GS</sub> - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

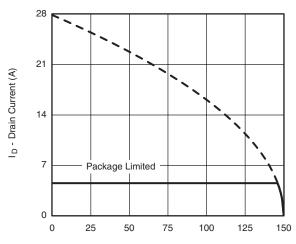


\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

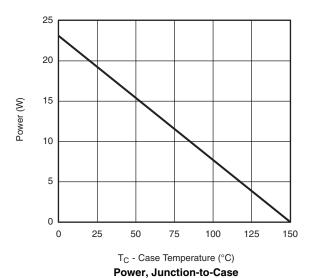


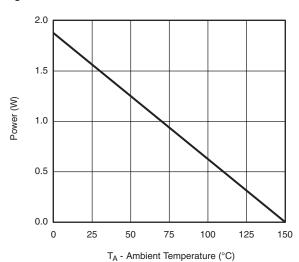
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T<sub>C</sub> - Case Temperature (°C)

#### **Current Derating\***





Power, Junction-to-Ambient

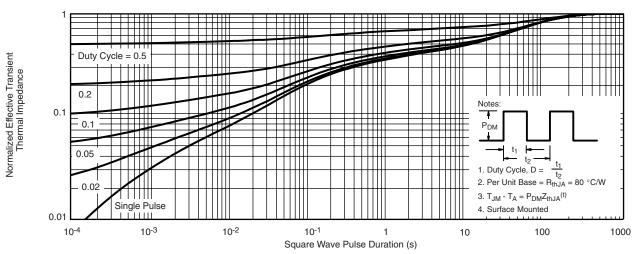
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

# SiA406DJ

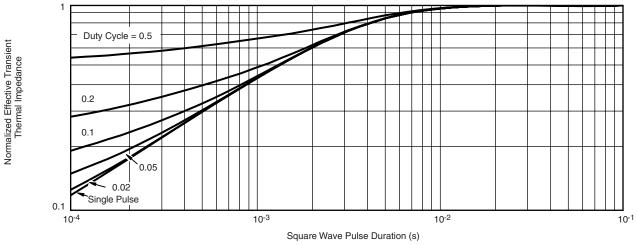
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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?65361">www.vishay.com/ppg?65361</a>.





## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
   Package outline exclusive of mold flash and metal burr
   Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS	INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP			0.010 TYP					
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1	0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Bey C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Revision: 02-Oct-12 Document Number: 91000

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IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF